

## PNP General Purpose Transistor

## MMBT589

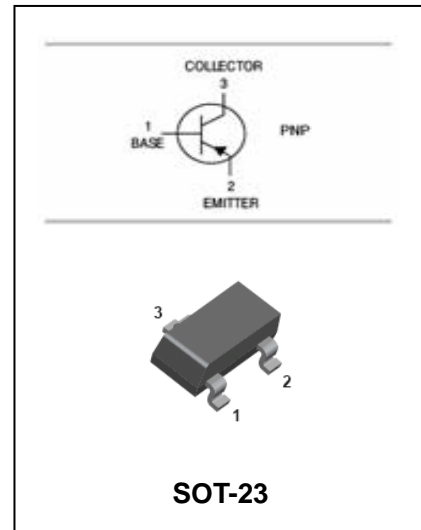
### FEATURES

- Epitaxial planar die construction.
- Also available in lead free version.



### APPLICATIONS

- High current surface mount PNP silicon switching transistor for load management in portable applications.



### ORDERING INFORMATION

Type No.	Marking	Package Code
MMBT589	589	SOT-23

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	UNIT
V <sub>CB0</sub>	collector-base voltage	-50	V
V <sub>CEO</sub>	collector-emitter voltage	-30	V
V <sub>EBO</sub>	emitter-base voltage	-5	V
I <sub>C</sub>	collector current (DC)	-1.0	A
P <sub>C</sub>	Collector dissipation	0.31	W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	403	°C/W
T <sub>J</sub> , T <sub>stg</sub>	junction and storage temperature	-55-150	°C

### ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

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Symbol	Parameter	Test conditions	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -100\mu A, I_E = 0$	-50		V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -10mA, I_B = 0$	-30		V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -100\mu A, I_C = 0$	-5		V
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = -30V$	-	-0.1	$\mu A$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = -4V$	-	-0.1	$\mu A$
$h_{FE}$	DC current gain	$V_{CE} = -2V; I_C = -1mA$ $V_{CE} = -2V; I_C = -500mA$ $V_{CE} = -2V; I_C = -1.0A$ $V_{CE} = -2V; I_C = -2.0A$	100 100 80 40	- 300 - -	
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C = -0.5A; I_B = -0.05A$ $I_C = -1.0A; I_B = -0.1A$ $I_C = -2.0A; I_B = -0.2A$	- - -	-0.25 -0.30 -0.65	V
$V_{BE(sat)}$	base-emitter saturation voltage	$I_C = -1.0A; I_B = -0.1A$	-	-1.2	V
$f_T$	transition frequency	$I_C = -100mA; V_{CE} = -5V;$ $f = 100MHz$	100	-	MHz
$C_{obo}$	Output capacitance	$f = 1.0MHz$	-	15	pF

### TYPICAL CHARACTERISTICS @ $T_a = 25^\circ C$ unless otherwise specified

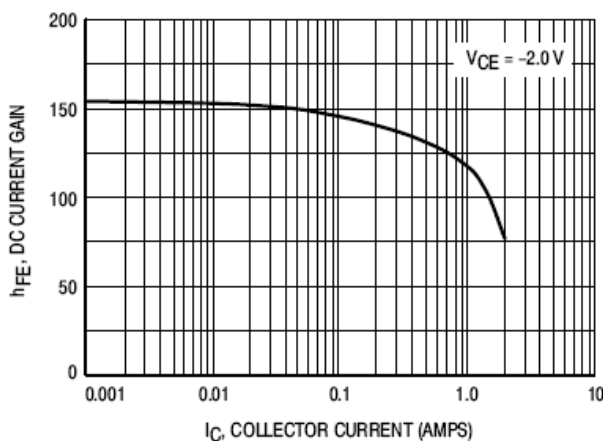


Figure 1. DC Current Gain versus Collector Current

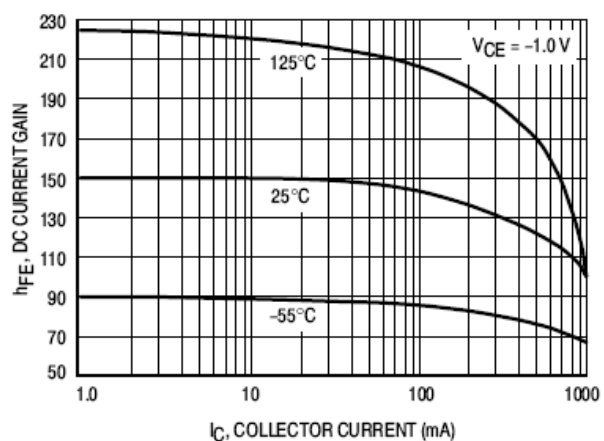


Figure 2. DC Current Gain versus Collector Current

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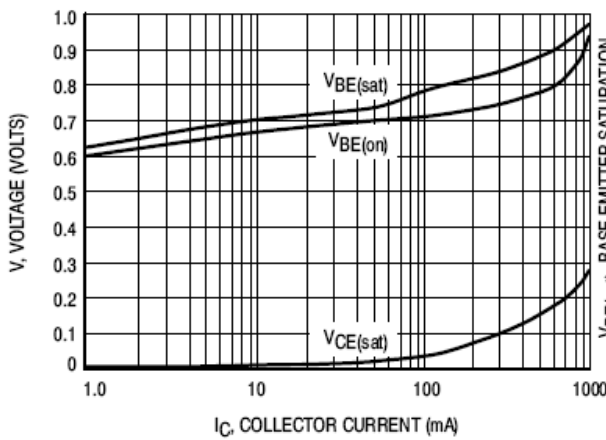


Figure 3. "On" Voltages

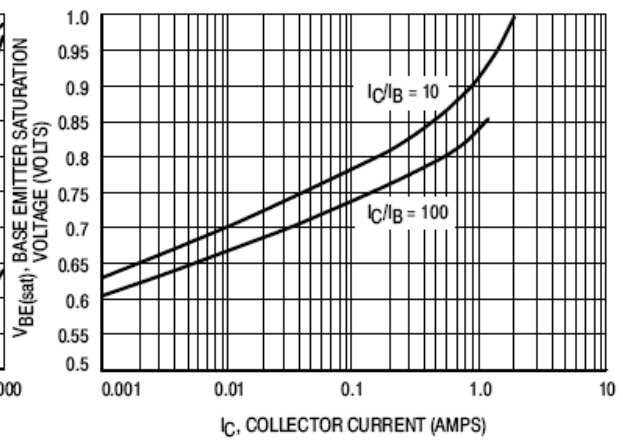


Figure 4. Base Emitter Saturation Voltage versus Collector Current

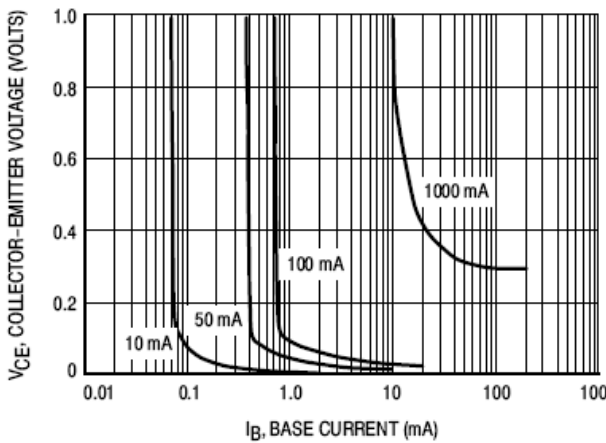


Figure 5. Collector Emitter Saturation Voltage versus Collector Current

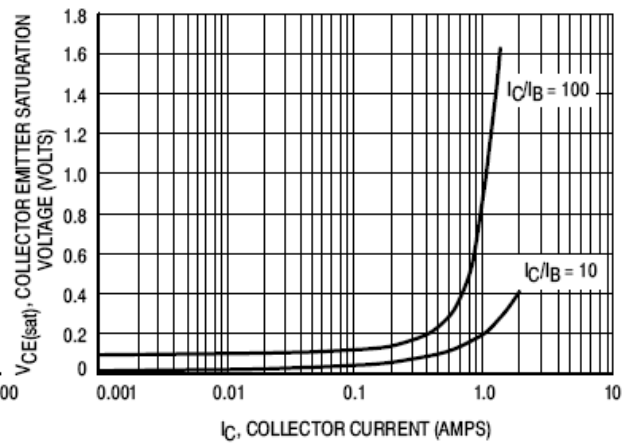


Figure 6. Collector Emitter Saturation Voltage versus Collector Current

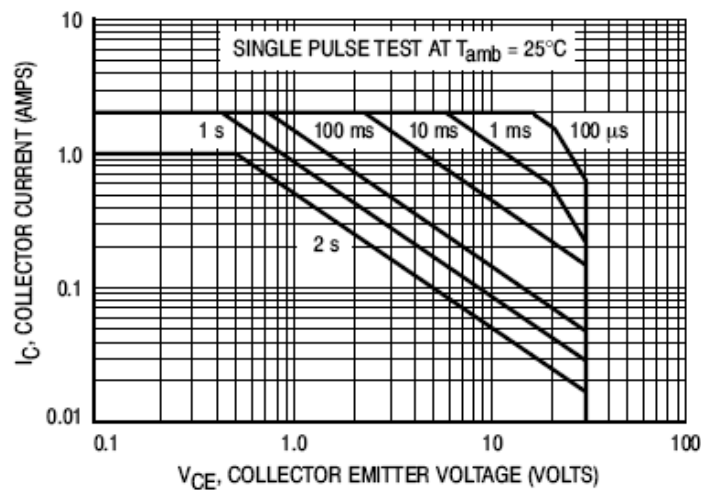


Figure 7. Safe Operating Area

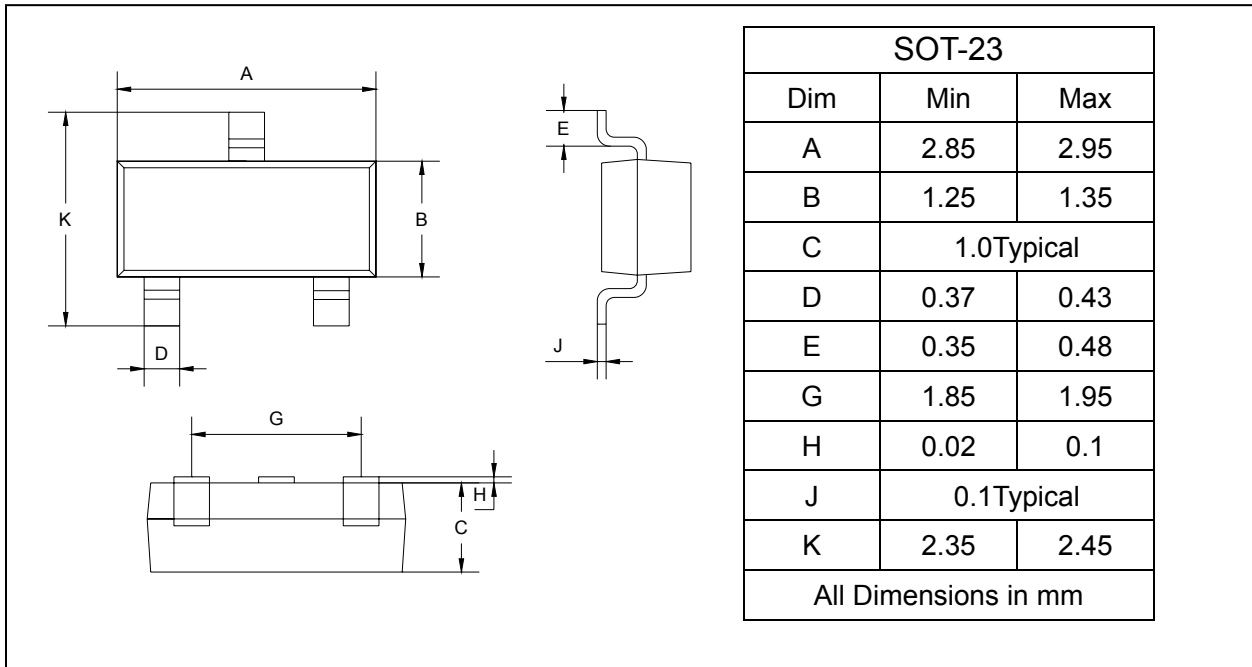
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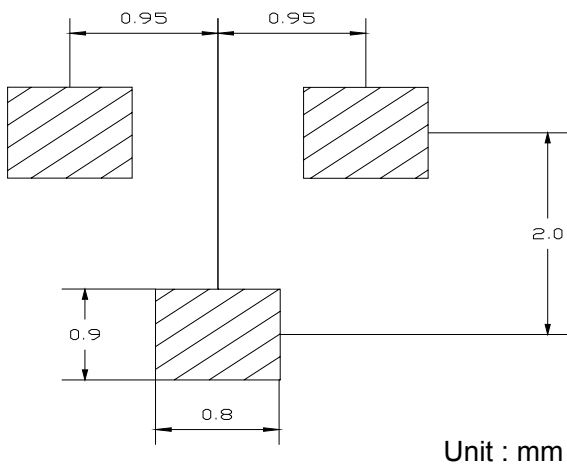
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

Device	Package	Shipping
MMBT589	SOT-23	3000/Tape&Reel